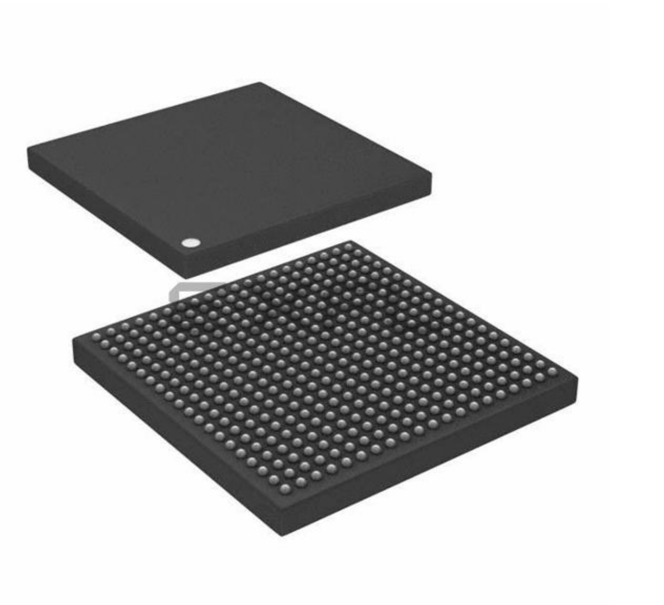

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Understanding Embedded - DSP (Digital Signal Processors)

Embedded - DSP (Digital Signal Processors) are specialized microprocessors designed to perform complex mathematical computations on digital signals in real-time. Unlike general-purpose processors, DSPs are optimized for high-speed numeric processing tasks, making them ideal for applications that require efficient and precise manipulation of digital data. These processors are fundamental in converting and processing signals in various forms, including audio, video, and communication signals, ensuring that data is accurately interpreted and utilized in embedded systems.

Applications of Embedded - DSP (Digital Signal Processors)

Details	
Product Status	Obsolete
Type	SC1400 Core
Interface	Host Interface, I²C, UART
Clock Rate	200MHz
Non-Volatile Memory	External
On-Chip RAM	80kB
Voltage - I/O	3.30V
Voltage - Core	1.20V
Operating Temperature	-40°C ~ 105°C (TJ)
Mounting Type	Surface Mount
Package / Case	400-LFBGA
Supplier Device Package	400-LFBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/msc7110vm800

Table 1. MSC7110 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
F11	V_{DDM}					
F12	GND					
F13	GND					
F14	GND					
F15	V_{DDIO}					
F16	V_{DDC}					
F17	V_{DDC}					
F18	NC					
F19	NC					
F20	NC					
G1	GND					
G2	D13					
G3	GND					
G4	V_{DDM}					
G5	V_{DDM}					
G6	GND					
G7	GND					
G8	GND					
G9	GND					
G10	GND					
G11	GND					
G12	GND					
G13	GND					
G14	GND					
G15	V_{DDIO}					
G16	V_{DDIO}					
G17	V_{DDC}					
G18	NC					
G19	NC					
G20	NC					
H1	D14					
H2	D12					
H3	D11					
H4	V_{DDM}					
H5	V_{DDM}					
H6	GND					
H7	GND					
H8	GND					

Table 1. MSC7110 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
M3	D5					
M4	V_{DDM}					
M5	V_{DDM}					
M6	GND					
M7	GND					
M8	GND					
M9	GND					
M10	GND					
M11	GND					
M12	GND					
M13	GND					
M14	GND					
M15	GND					
M16	V_{DDC}					
M17	V_{DDC}					
M18	GPIA14		$\overline{IRQ15}$	GPOA14	SDA	
M19	GPIA12		$\overline{IRQ3}$	GPOA12	UTXD	
M20	GPIA13		$\overline{IRQ2}$	GPOA13	URXD	
N1	D4					
N2	D6					
N3	V_{REF}					
N4	V_{DDM}					
N5	V_{DDM}					
N6	V_{DDM}					
N7	GND					
N8	GND					
N9	GND					
N10	GND					
N11	GND					
N12	GND					
N13	GND					
N14	GND					
N15	V_{DDIO}					
N16	V_{DDC}					
N17	V_{DDC}					
N18	CLKIN					
N19	GPIA15		$\overline{IRQ14}$	GPOA15	SCL	
N20	V_{SSPLL}					

Table 1. MSC7110 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
P1	D7					
P2	D17					
P3	D16					
P4	V_{DDM}					
P5	V_{DDM}					
P6	V_{DDM}					
P7	GND					
P8	GND					
P9	GND					
P10	GND					
P11	GND					
P12	GND					
P13	GND					
P14	GND					
P15	V_{DDIO}					
P16	V_{DDIO}					
P17	V_{DDC}					
P18	$\overline{\text{PORESET}}$					
P19	TPSEL					
P20	V_{DDPLL}					
R1	GND					
R2	D19					
R3	D18					
R4	V_{DDM}					
R5	V_{DDM}					
R6	V_{DDM}					
R7	GND					
R8	V_{DDM}					
R9	GND					
R10	V_{DDM}					
R11	GND					
R12	GND					
R13	V_{DDIO}					
R14	GND					
R15	V_{DDIO}					
R16	V_{DDIO}					
R17	V_{DDC}					
R18	TDO					

Table 1. MSC7110 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
U17	V_{DDC}					
U18	NC					
U19	TCK					
U20	$\overline{\text{TRST}}$					
V1	V_{DDM}					
V2	NC					
V3	A13					
V4	A11					
V5	A10					
V6	A5					
V7	A2					
V8	BA0					
V9	NC					
V10	reserved				EVNT0	
V11	SWTE	GPIA16	$\overline{\text{IRQ12}}$	GPOA16	EVNT4	
V12	GPIA8		$\overline{\text{IRQ6}}$	GPOA8	T0TCK	
V13	GPIA4		$\overline{\text{IRQ1}}$	GPOA4	reserved	
V14	GPIA0		$\overline{\text{IRQ11}}$	GPOA0	reserved	
V15	GPIA28		$\overline{\text{IRQ17}}$	GPOA28	reserved	reserved
V16	GPID6			GPOD6	reserved	reserved
V17	GPIA22		$\overline{\text{IRQ22}}$	GPOA22	reserved	
V18	GPIA24		$\overline{\text{IRQ24}}$	GPOA24	reserved	
V19	NC					
V20	TDI					
W1	GND					
W2	V_{DDM}					
W3	A12					
W4	A8					
W5	A7					
W6	A6					
W7	A3					
W8	NC					
W9	GPIA17		$\overline{\text{IRQ13}}$	GPOA17	EVNT1	CLKO
W10	BM0	GPIC14		GPOC14	EVNT2	
W11	GPIA10		$\overline{\text{IRQ5}}$	GPOA10	T0RFS	
W12	GPIA7		$\overline{\text{IRQ7}}$	GPOA7	T0TFS	
W13	GPIA3		$\overline{\text{IRQ8}}$	GPOA3	reserved	
W14	GPIA1		$\overline{\text{IRQ10}}$	GPOA1	reserved	

2.2 Recommended Operating Conditions

Table 3 lists recommended operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 3. Recommended Operating Conditions

Rating	Symbol	Value	Unit
Core supply voltage	V_{DDC}	1.14 to 1.26	V
Memory supply voltage	V_{DDM}	2.38 to 2.63	V
PLL supply voltage	V_{DDPLL}	1.14 to 1.26	V
I/O supply voltage	V_{DDIO}	3.14 to 3.47	V
Reference voltage	V_{REF}	1.19 to 1.31	V
Operating temperature range	T_J T_A	maximum: 105 minimum: –40	°C °C

2.3 Thermal Characteristics

Table 4 describes thermal characteristics of the MSC7110 for the MAP-BGA package.

Table 4. Thermal Characteristics for MAP-BGA Package

Characteristic	Symbol	MAP-BGA 17 × 17 mm[5]		Unit
		Natural Convection	200 ft/min (1 m/s) airflow	
Junction-to-ambient[1, 2]	$R_{\theta JA}$	39	31	°C/W
Junction-to-ambient, four-layer board[1, 3]	$R_{\theta JA}$	23	20	°C/W
Junction-to-board[4]	$R_{\theta JB}$	12		°C/W
Junction-to-case[5]	$R_{\theta JC}$	7		°C/W
Junction-to-package-top[6]	Ψ_{JT}	2		°C/W

Notes:
1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD 51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

Section 3.1, *Thermal Design Considerations* explains these characteristics in detail.

2.4 DC Electrical Characteristics

This section describes the DC electrical characteristics for the MSC7110.

Note: The leakage current is measured for nominal voltage values must vary in the same direction (for example, both V_{DDIO} and V_{DDC} vary by +2 percent or both vary by –2 percent).

Table 5. DC Electrical Characteristics

Characteristic	Symbol	Min	Typical	Max	Unit
Core and PLL voltage	V_{DDC} V_{DDPLL}	1.14	1.2	1.26	V
DRAM interface I/O voltage[1]	V_{DDM}	2.375	2.5	2.625	V
I/O voltage	V_{DDIO}	3.135	3.3	3.465	V
DRAM interface I/O reference voltage[2]	V_{REF}	$0.49 \times V_{DDM}$	1.25	$0.51 \times V_{DDM}$	V
DRAM interface I/O termination voltage[3]	VTT	$V_{REF} – 0.04$	V_{REF}	$V_{REF} + 0.04$	V
Input high CLKIN voltage	V_{IHCLK}	2.4	3.0	3.465	V
DRAM interface input high I/O voltage	V_{IHM}	$V_{REF} + 0.28$	V_{DDM}	$V_{DDM} + 0.3$	V
DRAM interface input low I/O voltage	V_{ILM}	–0.3	GND	$V_{REF} – 0.18$	V
Input leakage current, $V_{IN} = V_{DDIO}$	I_{IN}	–1.0	0.09	1	μA
V_{REF} input leakage current	I_{VREF}	—	—	5	μA
Tri-state (high impedance off state) leakage current, $V_{IN} = V_{DDIO}$	I_{OZ}	–1.0	0.09	1	μA
Signal low input current, $V_{IL} = 0.4$ V	I_L	–1.0	0.09	1	μA
Signal high input current, $V_{IH} = 2.0$ V	I_H	–1.0	0.09	1	μA
Output high voltage, $I_{OH} = –2$ mA, except open drain pins	V_{OH}	2.0	3.0	—	V
Output low voltage, $I_{OL}= 5$ mA	V_{OL}	—	0	0.4	V
Typical core power[5] • at 200 MHz • at 266 MHz (mask set 1M88B only)	P_C	 — —	 222 293	 — —	 mW mW

Notes:
1. The value of V_{DDM} at the MSC7110 device must remain within 50 mV of V_{DDM} at the DRAM device at all times.
2. V_{REF} must be equal to 50% of V_{DDM} and track V_{DDM} variations as measured at the receiver. Peak-to-peak noise must not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the MSC7110 device. It is the level measured at the far end signal termination. It should be equal to V_{REF}. This rail should track variations in the DC level of V_{REF}.
4. Output leakage for the memory interface is measured with all outputs disabled, $0 V \le V_{OUT} \le V_{DDM}$.
5. The core power values were measured.using a standard EFR pattern at typical conditions (25°C, 200 MHz or 266 MHz, 1.2 V core).

Table 6 lists the DDR DRAM capacitance.

Table 6. DDR DRAM Capacitance

Parameter/Condition	Symbol	Max	Unit
Input/output capacitance: DQ, DQS	C_{IO}	30	pF
Delta input/output capacitance: DQ, DQS	C_{DIO}	30	pF

Note: These values were measured under the following conditions:
- $V_{DDM} = 2.5$ V ± 0.125 V
- f = 1 MHz
- $T_A = 25$°C
- $V_{OUT} = V_{DDM}/2$
- V_{OUT} (peak to peak) = 0.2 V

Table 13. Resulting Ranges Permitted for the Core Clock

CLKCTRL[CKSEL]	CLKCTRL[RNG]	Resulting Division Factor	Allowed Range of Core Clock	Comments
11	1	1	Reserved	Reserved
11	0	2	150 ≤ Core_Clk ≤ 200 MHz	Limited by range of PLL
01	1	2	150 ≤ Core_Clk ≤ 200 MHz	Limited by range of PLL
01	0	4	75 ≤ Core_Clk ≤ 150 MHz	Limited by range of PLL
Note: This table results from the allowed range for F_{OUT}, which depends on clock selected via CLKCTRL[CKSEL].				

2.5.2.5 Core Clock Frequency Range When Using DDR Memory

The core clock can also be limited by the frequency range of the DDR devices in the system. **Table 14** summarizes this restriction.

Table 14. Core Clock Ranges When Using DDR

DDR Type	Allowed Frequency Range for DDR CK	Corresponding Range for the Core Clock	Comments
DDR 200 (PC-1600)	83–100 MHz	166 ≤ core clock ≤ 200 MHz	Core limited to 2 × maximum DDR frequency
DDR 266 (PC-2100)	83–133 MHz	166 ≤ core clock ≤ 266 MHz	Core limited to 2 × maximum DDR frequency
DDR 333 (PC-2600)	83–150 MHz	166 ≤ core clock ≤ 300 MHz	Core limited to 2 × maximum DDR frequency

2.5.3 Reset Timing

The MSC7110 device has several inputs to the reset logic. All MSC7110 reset sources are fed into the reset controller, which takes different actions depending on the source of the reset. The reset status register indicates the most recent sources to cause a reset. **Table 15** describes the reset sources.

Table 15. Reset Sources

Name	Direction	Description
Power-on reset (PORESET)	Input	Initiates the power-on reset flow that resets the MSC7110 and configures various attributes of the MSC7110. On PORESET, the entire MSC7110 device is reset. SPLL and DLL states are reset, HRESET is driven, the SC1400 extended core is reset, and system configuration is sampled. The system is configured only when PORESET is asserted.
External Hard reset (HRESET)	Input/ Output	Initiates the hard reset flow that configures various attributes of the MSC7110. While HRESET is asserted, HRESET is an open-drain output. Upon hard reset, HRESET is driven and the SC1400 extended core is reset.
Software watchdog reset	Internal	When the MSC7110 watchdog count reaches zero, a software watchdog reset is signalled. The enabled software watchdog event then generates an internal hard reset sequence.
Bus monitor reset	Internal	When the MSC7110 bus monitor count reaches zero, a bus monitor hard reset is asserted. The enabled bus monitor event then generates an internal hard reset sequence.
JTAG EXTEST, CLAMP, or HIGHZ command	Internal	When a Test Access Port (TAP) executes an EXTEST, CLAMP, or HIGHZ command, the TAP logic asserts an internal reset signal that generates an internal soft reset sequence.

Table 16 summarizes the reset actions that occur as a result of the different reset sources.

2.5.4.2 DDR DRAM Output AC Timing Specifications

Table 19 and **Table 20** list the output AC timing specifications and measurement conditions for the DDR DRAM interface.

Table 19. DDR DRAM Output AC Timing

No.	Parameter	Symbol	Min		Max	Unit
			Mask Set 1L44X	Mask Set 1M88B		
200	CK cycle time, (CK/$\overline{CK}$ crossing)[1] • 100 MHz (DDR200) • 133 MHz (DDR266)	t_{CK}	10 Not applicable	1.0 7.52	— —	ns ns
204	An/$\overline{RAS}$/$\overline{CAS}$/$\overline{WE}$/CKE output setup with respect to CK	t_{DDKHAS}	$0.5 \times t_{CK} - 2250$	$0.5 \times t_{CK} - 1000$	—	ps
205	An/$\overline{RAS}$/$\overline{CAS}$/$\overline{WE}$/CKE output hold with respect to CK	t_{DDKHAX}	$0.5 \times t_{CK} - 1250$	$0.5 \times t_{CK} - 1000$	—	ps
206	$\overline{CSn}$ output setup with respect to CK	t_{DDKHCS}	$0.5 \times t_{CK} - 2250$	$0.5 \times t_{CK} - 1000$	—	ps
207	$\overline{CSn}$ output hold with respect to CK	t_{DDKHCX}	$0.5 \times t_{CK} - 1250$	$0.5 \times t_{CK} - 1000$	—	ps
208	CK to DQSn[2]	t_{DDKHMH}	–600	–600	600	ps
209	Dn/DQMn output setup with respect to DQSn[3]	t_{DDKHDS}, t_{DDKLDS}	$0.25 \times t_{MCK} - 1050$	$0.25 \times t_{CK} - 750$	—	ps
210	Dn/DQMn output hold with respect to DQSn[3]	t_{DDKHDX}, t_{DDKLDX}	$0.25 \times t_{CK} - 1050$	$0.25 \times t_{CK} - 750$	—	ps
211	DQSn preamble start[4]	t_{DDKHMP}	$-0.25 \times t_{CK}$	$-0.25 \times t_{CK}$	—	ps
212	DQSn epilogue end[5]	t_{DDKHME}	–600	–600	600	ps

Notes:
1. All CK/$\overline{CK}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
2. t_{DDKHMH} can be modified through the TCFG2[WRDD] DQSS override bits. The DRAM requires that the first write data strobe arrives 75–125% of a DRAM cycle after the write command is issued. Any skew between DQSn and CK must be considered when trying to achieve this 75%–125% goal. The TCFG2[WRDD] bits can be used to shift DQSn by 1/4 DRAM cycle increments. The skew in this case refers to an internal skew existing at the signal connections. By default, the CK/$\overline{CK}$ crossing occurs in the middle of the control signal (An/$\overline{RAS}$/$\overline{CAS}$/$\overline{WE}$/CKE) tenure. Setting TCFG2[ACSM] bit shifts the control signal assertion 1/2 DRAM cycle earlier than the default timing. This means that the signal is asserted no earlier than 410 ps before the CK/$\overline{CK}$ crossing and no later than 677 ps after the crossing time; the device uses 1087 ps of the skew budget (the interval from –410 to +677 ps). Timing is verified by referencing the falling edge of CK. See Chapter 10 of the *MSC711x Reference Manual* for details.
3. Determined by maximum possible skew between a data strobe (DQS) and any corresponding bit of data. The data strobe should be centered inside of the data eye.
4. Please note that this spec is in reference to the DQSn first rising edge. It could also be referenced from CK(r), but due to programmable delay of the write strobes (TCFG2[WRDD]), there pre-amble may be extended for a full DRAM cycle. For this reason, we reference from DQSn.
5. All outputs are referenced to the rising edge of CK. Note that this is essentially the CK/DQSn skew in spec 208. In addition there is no real “maximum” time for the epilogue end. JEDEC does not require this is as a device limitation, but simply for the chip to guarantee fast enough write to read turn-around times. This is already guaranteed by the memory controller operation.

Table 21. TDM Timing

No.	Characteristic	Expression	Min	Max	Units
307	TDMxTCK High to TDMxTD output valid		—	14.0	ns
308	TDMxTD hold time		2.0	—	ns
309	TDMxTCK High to TDMxTD output high impedance		—	10.0	ns
310	TDMXTFS/TDMxRFS output valid		—	13.5	ns
311	TDMxTFS/TDMxRFS output hold time		2.5	—	ns

Notes:
1. Output values are based on 30 pF capacitive load.
2. Inputs are referenced to the sampling that the TDM is programmed to use. Outputs are referenced to the programming edge they are programmed to use. Use of the rising edge or falling edge as a reference is programmable. Refer to the *MSC711x Reference Manual* for details. TDMxTCK and TDMxRCK are shown using the rising edge.

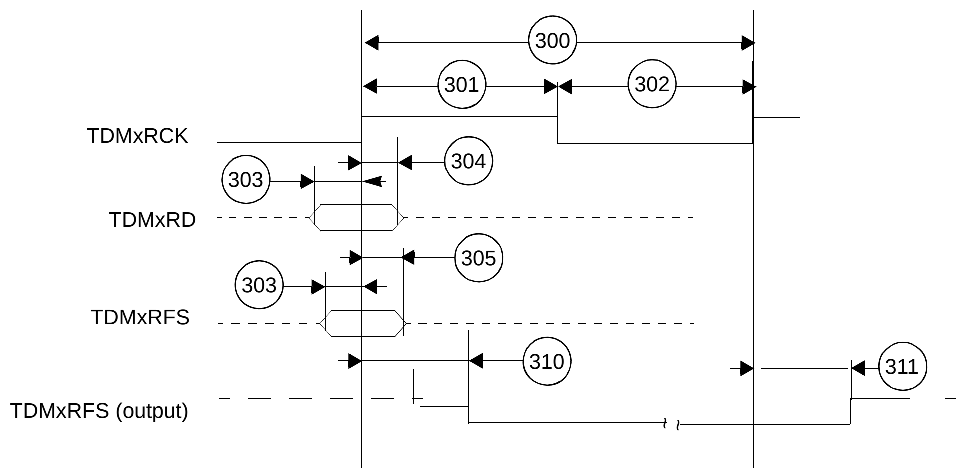

Figure 8. TDM Receive Signals

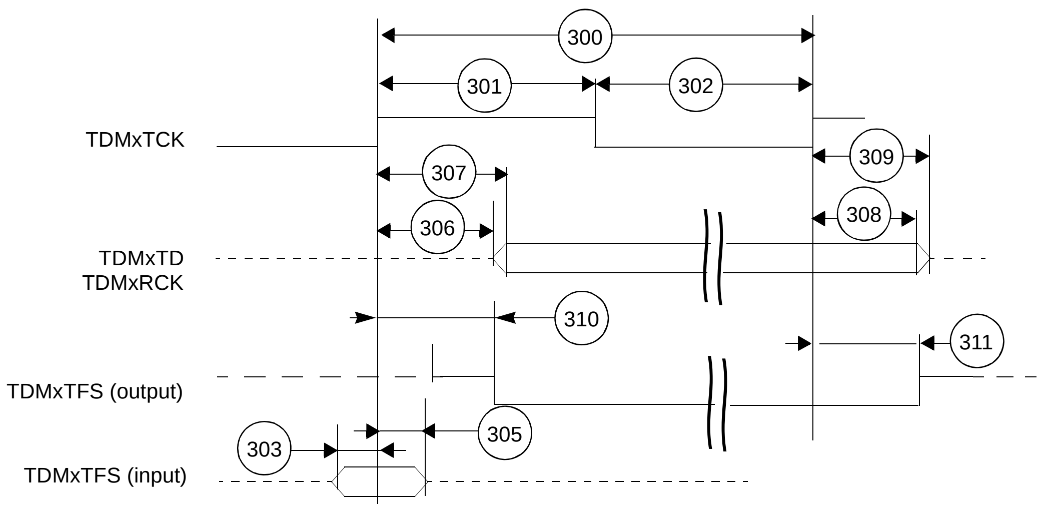

Figure 9. TDM Transmit Signals

2.5.6 HDI16 Signals

Table 22. Host Interface (HDI16) Timing[1, 2]

No.	Characteristics[3]	Mask Set 1L44X		Mask Set 1M88B		Unit
		Expression	Value	Expression	Value	
40	Host Interface Clock period	T_{HCLK}	Note 1	T_{CORE}	Note 1	ns

Table 22. Host Interface (HDI16) Timing[1, 2] (continued)

No.	Characteristics[3]	Mask Set 1L44X		Mask Set 1M88B		Unit
		Expression	Value	Expression	Value	
44a	Read data strobe minimum assertion width[4] HACK read minimum assertion width	$3.0 \times T_{HCLK}$	Note 11	$2.0 \times T_{CORE} + 9.0$	Note 11	ns
44b	Read data strobe minimum deassertion width[4] HACK read minimum deassertion width	$1.5 \times T_{HCLK}$	Note 11	$1.5 \times T_{CORE}$	Note 11	ns
44c	Read data strobe minimum deassertion width[4] after “Last Data Register” reads[5,6], or between two consecutive CVR, ICR, or ISR reads[7] HACK minimum deassertion width after “Last Data Register” reads[5,6]	$2.5 \times T_{HCLK}$	Note 11	$2.5 \times T_{CORE}$	Note 11	ns
45	Write data strobe minimum assertion width[8] HACK write minimum assertion width	$1.5 \times T_{HCLK}$	Note 11	$1.5 \times T_{CORE}$	Note 11	ns
46	Write data strobe minimum deassertion width[8] HACK write minimum deassertion width after ICR, CVR and Data Register writes[5]	$2.5 \times T_{HCLK}$	Note 11	$2.5 \times T_{CORE}$	Note 11	ns
47	Host data input minimum setup time before write data strobe deassertion[8] Host data input minimum setup time before HACK write deassertion	—	3.0	—	2.5	ns
48	Host data input minimum hold time after write data strobe deassertion[8] Host data input minimum hold time after HACK write deassertion	—	4.0	—	2.5	ns
49	Read data strobe minimum assertion to output data active from high impedance[4] HACK read minimum assertion to output data active from high impedance	—	1.0	—	1.0	ns
50	Read data strobe maximum assertion to output data valid[4] HACK read maximum assertion to output data valid	$(2.0 \times T_{HCLK}) + 8.0$	Note 11	$(2.0 \times T_{CORE}) + 8.0$	Note 11	ns
51	Read data strobe maximum deassertion to output data high impedance[4] HACK read maximum deassertion to output data high impedance	—	8.0	—	9.0	ns
52	Output data minimum hold time after read data strobe deassertion[4] Output data minimum hold time after HACK read deassertion	—	1.0	—	1.0	ns
53	HCS[1–2] minimum assertion to read data strobe assertion[4]	—	0.0	—	0.5	ns
54	HCS[1–2] minimum assertion to write data strobe assertion[8]	—	0.0	—	0.0	ns
55	HCS[1–2] maximum assertion to output data valid	$(2.0 \times T_{HCLK}) + 8.0$	Note 11	$(2.0 \times T_{CORE}) + 6.0$	Note 11	ns
56	HCS[1–2] minimum hold time after data strobe deassertion[9]	—	0.0	—	0.5	ns
57	HA[0–3], HRW minimum setup time before data strobe assertion[9]	—	5.0	—	5.0	ns
58	HA[0–3], HRW minimum hold time after data strobe deassertion[9]	—	5.0	—	5.0	ns
61	Maximum delay from read data strobe deassertion to host request deassertion for “Last Data Register” read[4, 5, 10]	$(3.0 \times T_{HCLK}) + 8.0$	Note 11	$(3.0 \times T_{CORE}) + 6.0$	Note 11	ns
62	Maximum delay from write data strobe deassertion to host request deassertion for “Last Data Register” write[5,8,10]	$(3.0 \times T_{HCLK}) + 8.0$	Note 11	$(3.0 \times T_{CORE}) + 6.0$	Note 11	ns
63	Minimum delay from DMA HACK (OAD=0) or Read/Write data strobe(OAD=1) deassertion to HREQ assertion.	$(2.0 \times T_{HCLK}) + 1.0$	Note 11	$(2.0 \times T_{CORE}) + 1.0$	Note 11	ns
64	Maximum delay from DMA HACK (OAD=0) or Read/Write data strobe(OAD=1) assertion to HREQ deassertion	$(5.0 \times T_{HCLK}) + 8.0$	Note 11	$(5.0 \times T_{CORE}) + 6.0$	Note 11	ns

2.5.7 I²C Timing

Table 23. I²C Timing

No.	Characteristic	Fast		Unit
		Min	Max	
450	SCL clock frequency	0	400	kHz
451	Hold time START condition	(Clock period/2) – 0.3	—	µs
452	SCL low period	(Clock period/2) – 0.3	—	µs
453	SCL high period	(Clock period/2) – 0.1	—	µs
454	Repeated START set-up time (not shown in figure)	$2 \times 1/F_{BCK}$	—	µs
455	Data hold time	0	—	µs
456	Data set-up time	250	—	ns
457	SDA and SCL rise time	—	700	ns
458	SDA and SCL fall time	—	300	ns
459	Set-up time for STOP	(Clock period/2) – 0.7	—	µs
460	Bus free time between STOP and START	(Clock period/2) – 0.3	—	µs
Note:	SDA set-up time is referenced to the rising edge of SCL. SDA hold time is referenced to the falling edge of SCL. Load capacitance on SDA and SCL is 400 pF.			

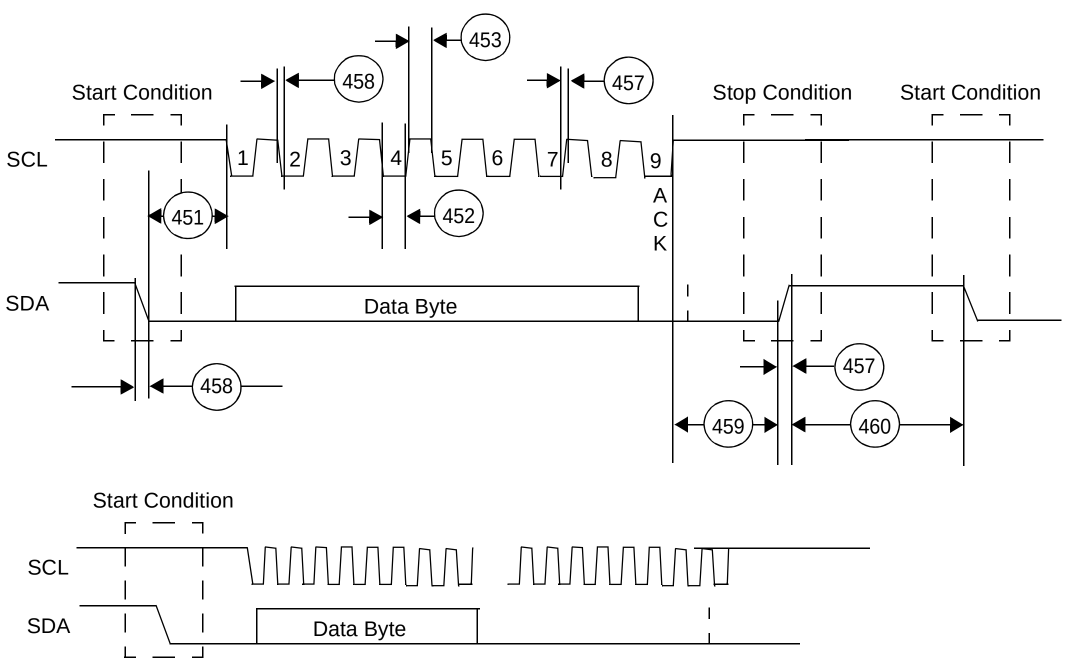

Figure 16. I²C Timing Diagram

2.5.8 UART Timing

Table 24. UART Timing

No.	Characteristics	Expression	Mask Set 1L44X		Mask Set 1M88B		Unit
			Min	Max	Min	Max	
—	Internal bus clock (APBCLK)	$F_{CORE}/2$	—	100	—	133	MHz
—	Internal bus clock period (1/APBCLK)	T_{APBCLK}	10.0	—	7.52	—	ns
400	URXD and UTXD inputs high/low duration	$16 \times T_{APBCLK}$	160.0	—	120.3	—	ns
401	URXD and UTXD inputs rise/fall time		—	5	—	5	ns
402	UTXD output rise/fall time		—	5	—	5	ns

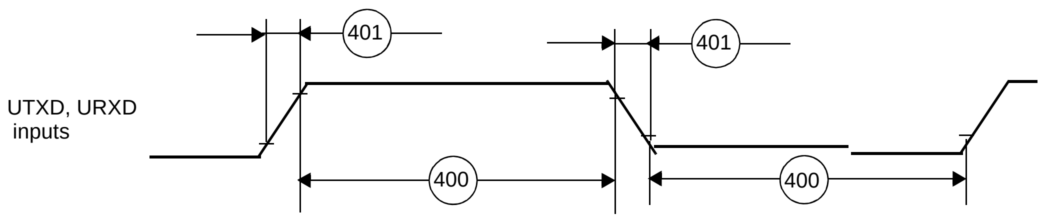

Figure 17. UART Input Timing

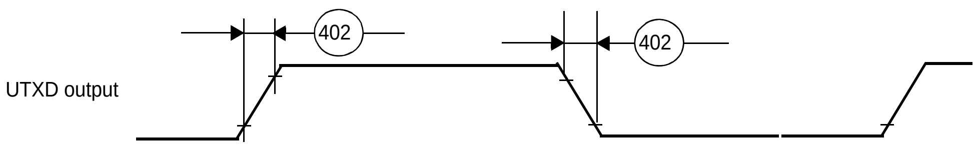

Figure 18. UART Output Timing

2.5.9 EE Timing

Table 25. EE0 Timing

Number	Characteristics	Type	Min
65	EE0 input to the core	Asynchronous	4 core clock periods
66	EE0 output from the core	Synchronous to core clock	1 core clock period

Notes:
1. The core clock is the SC1400 core clock. The ratio between the core clock and CLKOUT is configured during power-on-reset.
2. Configure the direction of the EE pin in the EE_CTRL register (see the *SC1400 Core Reference Manual* for details.
3. Refer to **Table 15** for details on EE pin functionality.

Figure 19 shows the signal behavior of the EE pin.

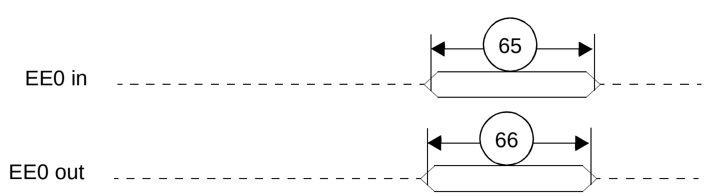

Figure 19. EE Pin Timing

3.2 Power Supply Design Considerations

This section outlines the MSC7110 power considerations: power supply, power sequencing, power planes, decoupling, power supply filtering, and power consumption. It also presents a recommended power supply design and options for low-power consumption. For information on AC/DC electrical specifications and thermal characteristics, refer to **Section 2**.

3.2.1 Power Supply

The MSC7110 requires four input voltages, as shown in **Table 29**.

Table 29. MSC7110 Voltages

Voltage	Symbol	Value
Core	V_{DDC}	1.2 V
Memory	V_{DDM}	2.5 V
Reference	V_{REF}	1.25 V
I/O	V_{DDIO}	3.3 V

You should supply the MSC7110 core voltage via a variable switching supply or regulator to allow for compatibility with possible core voltage changes on future silicon revisions. The core voltage is supplied with 1.2 V (+5% and –10%) across V_{DDC} and GND and the I/O section is supplied with 3.3 V (± 10%) across V_{DDIO} and GND. The memory and reference voltages supply the DDR memory controller block. The memory voltage is supplied with 2.5 V across V_{DDM} and GND. The reference voltage is supplied across V_{REF} and GND and must be between $0.49 \times V_{DDM}$ and $0.51 \times V_{DDM}$. Refer to the JEDEC standard JESD8 (*Stub Series Terminated Logic for 2.5 Volts* (STTL_2)) for memory voltage supply requirements.

3.2.2 Power Sequencing

One consequence of multiple power supplies is that the voltage rails ramp up at different rates when power is initially applied. The rates depend on the power supply, the type of load on each power supply, and the way different voltages are derived. It is extremely important to observe the power up and power down sequences at the board level to avoid latch-up, forward biasing of ESD devices, and excessive currents, which all lead to severe device damage.

Note: There are five possible power-up/power-down sequence cases. The first four cases listed in the following sections are recommended for new designs. The fifth case is not recommended for new designs and must be carefully evaluated for current spike risks based on actual information for the specific application.

3.2.2.1 Case 1

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V) supply second.
3. Turn on the V_{DDM} (2.5 V) supply third.
4. Turn on the V_{REF} (1.25 V) supply fourth (last).

The power-down sequence is as follows:

1. Turn off the V_{REF} (1.25 V) supply first.
2. Turn off the V_{DDM} (2.5 V) supply second.
3. Turn off the V_{DDC} (1.2 V) supply third.
4. Turn of the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down of V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 26** for relative timing for power sequencing case 1.

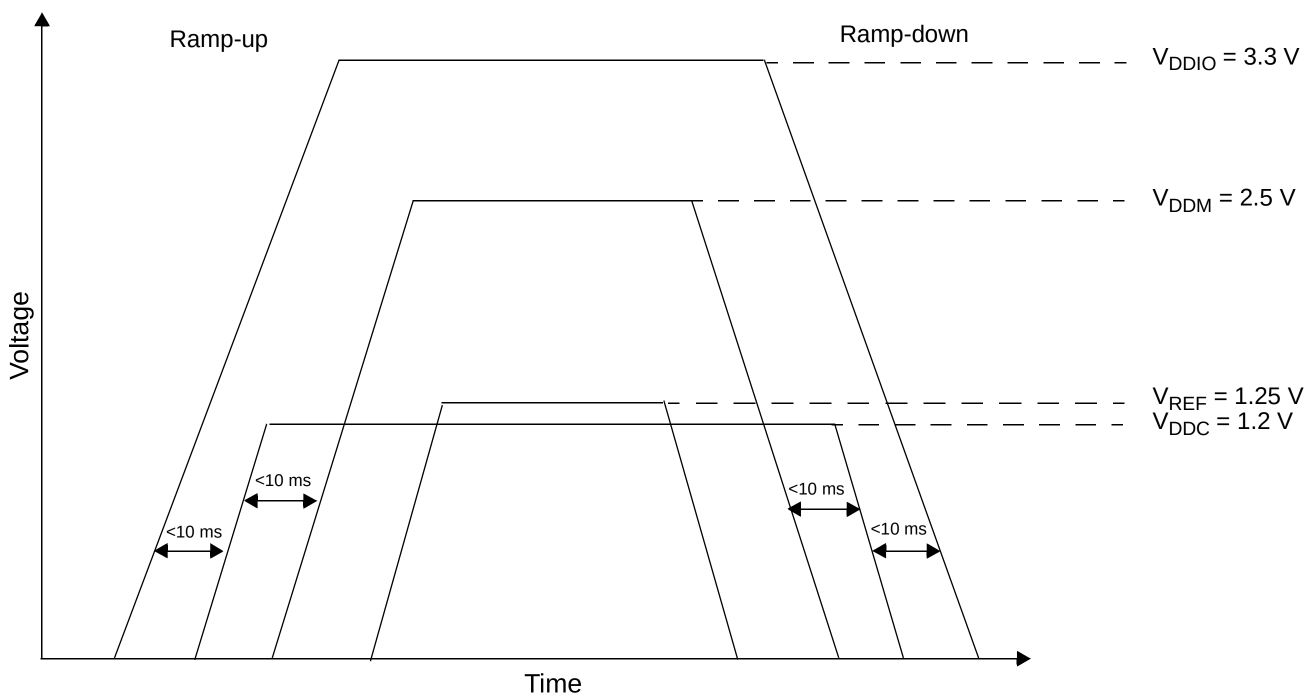

Figure 26. Voltage Sequencing Case 1

3.2.2.2 Case 2

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V) and V_{DDM} (2.5 V) supplies simultaneously (second).
3. Turn on the V_{REF} (1.25 V) supply last (third).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC}/V_{DDM} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{REF} (1.25 V) supply first.
2. Turn off the V_{DDM} (2.5 V) supply second.
3. Turn off the V_{DDC} (1.2 V) supply third.
4. Turn of the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down for V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 27** for relative timing for Case 2.

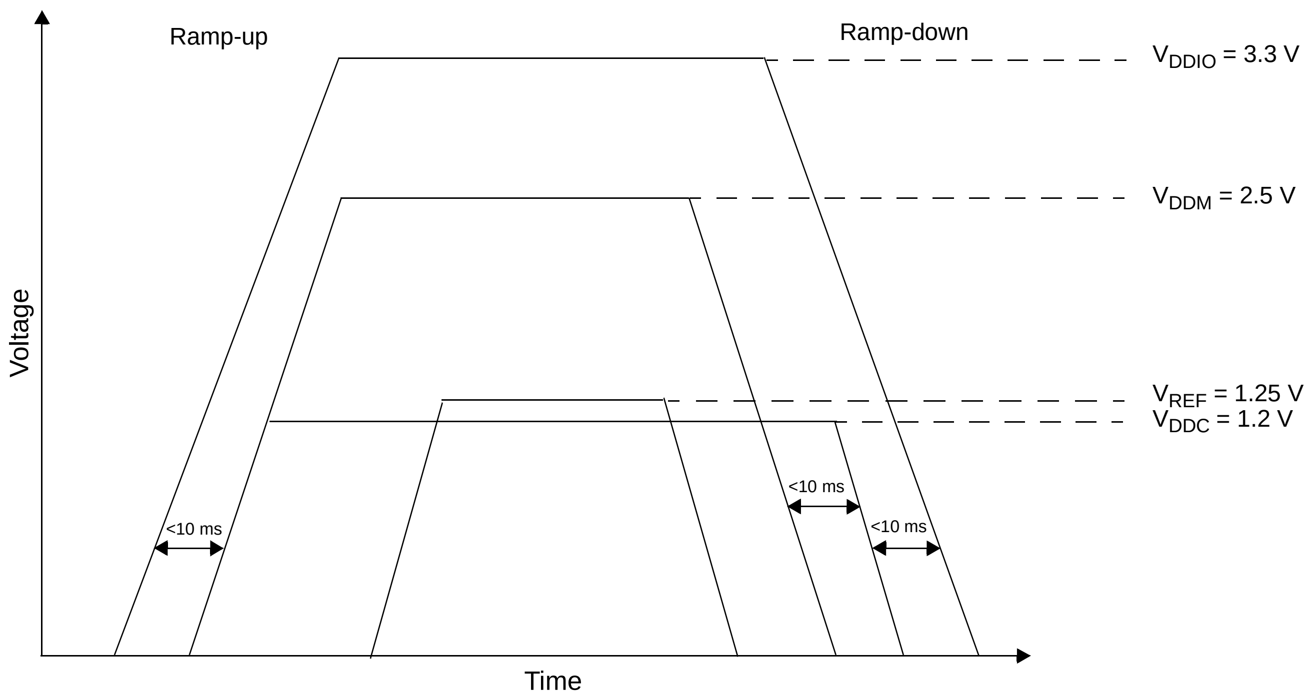

Figure 27. Voltage Sequencing Case 2

3.2.2.4 Case 4

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V), V_{DDM} (2.5 V), and V_{REF} (1.25 V) supplies simultaneously (second).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{DDC} (1.2 V), V_{REF} (1.25 V), and V_{DDM} (2.5 V) supplies simultaneously (first).
2. Turn of the V_{DDIO} (3.3 V) supply last.

Use the following guidelines:

- Make sure that the time interval between the ramp-up or ramp-down time for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 29** for relative timing for Case 4.

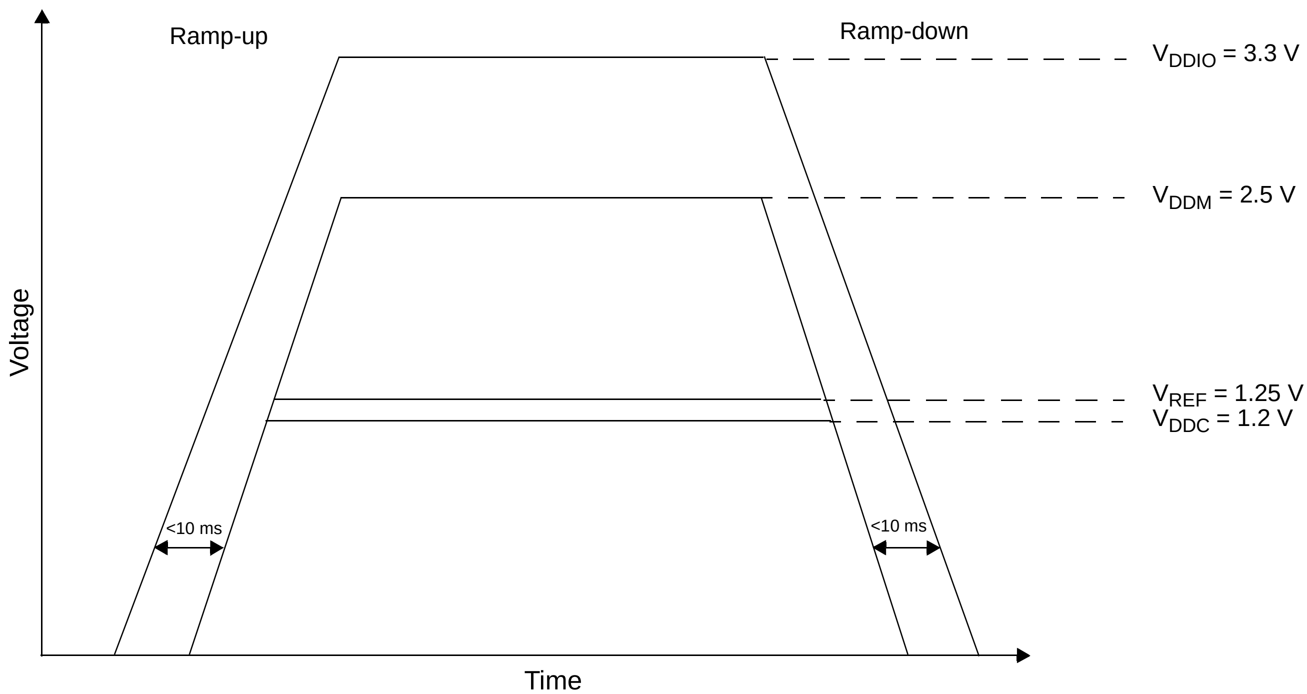

Figure 29. Voltage Sequencing Case 4

3.3.2 Peripheral Power

Peripherals include the DDR memory controller, DMA controller, HDI16, TDM, UART, timers, GPIOs, and the I^2C module. Basic power consumption by each module is assumed to be the same and is computed by using the following equation which assumes an effective load of 20 pF, core voltage swing of 1.2 V, and a switching frequency of 100 MH or 133 MHz. This yields:

$$P_{PERIPHERAL} = 20\ pF \times (1.2\ V)^2 \times 100\ MHz \times 10^{-3} = 2.88\ mW\ per\ peripheral \quad \text{Eqn. 7}$$

$$P_{PERIPHERAL} = 20\ pF \times (1.2\ V)^2 \times 133\ MHz \times 10^{-3} = 3.83\ mW\ per\ peripheral \quad \text{Eqn. 8}$$

Multiply this value by the number of peripherals used in the application to compute the total peripheral power consumption.

3.3.3 External Memory Power

Estimation of power consumption by the DDR memory system is complex. It varies based on overall system signal line usage, termination and load levels, and switching rates. Because the DDR memory includes terminations external to the MSC7110 device, the 2.5 V power source provides the power for the termination, which is a static value of 16 mA per signal driven high. The dynamic power is computed, however, using a differential voltage swing of ±0.200 V, yielding a peak-to-peak swing of 0.4 V. The equations for computing the DDR power are:

$$P_{DDRIO} = P_{STATIC} + P_{DYNAMIC} \quad \text{Eqn. 9}$$

$$P_{STATIC} = (unused\ pins \times \%\ driven\ high) \times 16\ mA \times 2.5\ V \quad \text{Eqn. 10}$$

$$P_{DYNAMIC} = (pin\ activity\ value) \times 20\ pF \times (0.4\ V)^2 \times 200\ MHz \times 10^{-3}\ mW \quad \text{Eqn. 11}$$

$$P_{DYNAMIC} = (pin\ activity\ value) \times 20\ pF \times (0.4\ V)^2 \times 266\ MHz \times 10^{-3}\ mW \quad \text{Eqn. 12}$$

$$pin\ activity\ value = (active\ data\ lines \times \%\ activity \times \%\ data\ switching) + (active\ address\ lines \times \%\ activity) \quad \text{Eqn. 13}$$

As an example, assume the following:

unused pins = 16 (DDR uses 16-pin mode)
% driven high = 50%
active data lines = 16
% activity = 60%
% data switching = 50%
active address lines = 3

In this example, the DDR memory power consumption is:

$$P_{DDRIO} = ((16 \times 0.5) \times 16 \times 2.5) + (((16 \times 0.6 \times 0.5) + (3 \times 0.6)) \times 20 \times (0.4)^2 \times 200 \times 10^{-3}) = 324.2\ mW \quad \text{Eqn. 14}$$

$$P_{DDRIO} = ((16 \times 0.5) \times 16 \times 2.5) + (((16 \times 0.6 \times 0.5) + (3 \times 0.6)) \times 20 \times (0.4)^2 \times 266 \times 10^{-3}) = 326.3\ mW \quad \text{Eqn. 15}$$

3.4.3.2 I^2C Boot

When the MSC7110 device is configured to boot from the I^2C port, the boot program configures the GPIO pins shared with the I^2C pins as I^2C pins. The I^2C interface is configured as follows:

- I^2C in master mode.
- EPROM in slave mode.

For details on the boot procedure, see the “Boot Program” chapter of the *MSC711x Reference Manual*.

3.5 DDR Memory System Guidelines

MSC7110 devices contain a memory controller that provides a glueless interface to external double data rate (DDR) SDRAM memory modules with Class 2 Series Stub Termination Logic 2.5 V (SSTL_2). There are two termination techniques, as shown in Figure 32. Technique B is the most popular termination technique.

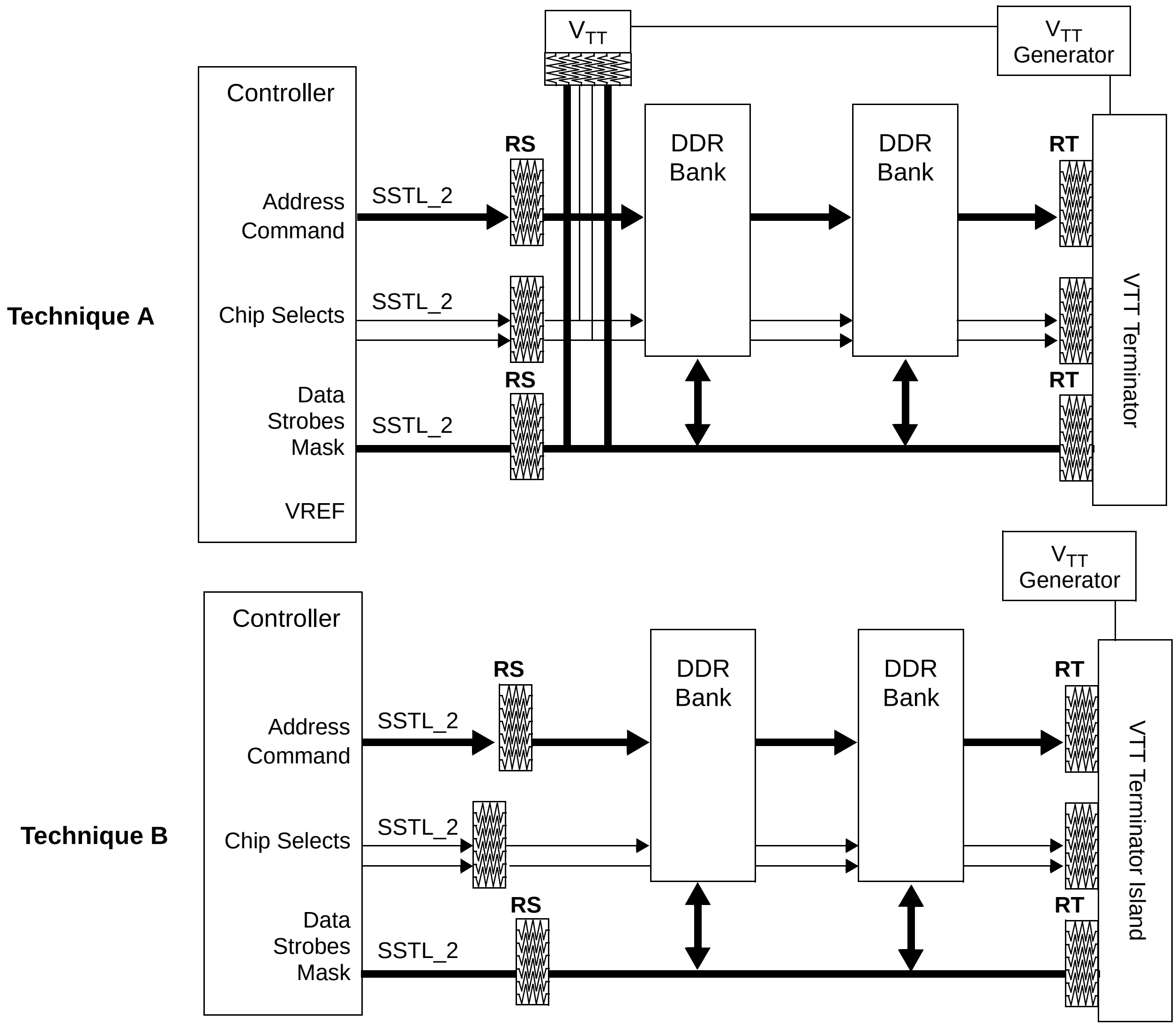

Figure 32. SSTL Termination Techniques

Figure 33 illustrates the power wattage for the resistors. Typical values for the resistors are as follows:

- RS = 22 Ω
- RT = 24 Ω

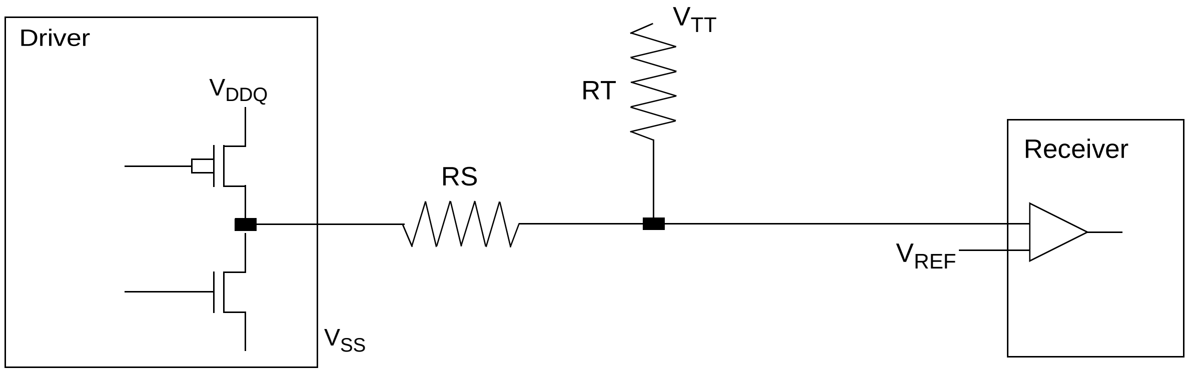

Figure 33. SSTL Power Value

3.5.1 V_{REF} and V_{TT} Design Constraints

V_{TT} and V_{REF} are isolated power supplies at the same voltage, with V_{TT} as a high current power source. This section outlines the voltage supply design needs and goals:

- Minimize the noise on both rails.
- V_{TT} must track variation in the V_{REF} DC offsets. Although they are isolated supplies, one possible solution is to use a single IC to generate both signals.
- Both references should have minimal drift over temperature and source supply.
- It is important to minimize the noise from coupling onto V_{REF} as follows:
  - Isolate V_{REF} and shield it with a ground trace.
  - Use 15–20 mm track.
  - Use 20–30 mm clearance between other traces for isolating.
  - Use the outer layer route when possible.
  - Use distributed decoupling to localize transient currents and return path and decouple with an inductance less than 3 nH.
- Max source/sink transient currents of up to 1.8 A for a 32-bit data bus.
- Use a wide island trace on the outer layer:
  - Place the island at the end of the bus.
  - Decouple both ends of the bus.
  - Use distributed decoupling across the island.
  - Place SSTL termination resistors inside the V_{TT} island and ensure a good, solid connection.
- Place the V_{TT} regulator as closely as possible to the termination island.
  - Reduce inductance and return path.
  - Tie current sense pin at the midpoint of the island.

3.5.2 Decoupling

The DDR decoupling considerations are as follows:

- DDR memory requires significantly more burst current than previous SDRAMs.
- In the worst case, up to 64 drivers may be switching states.
- Pay special attention and decouple discrete ICs per manufacturer guidelines.
- Leverage V_{TT} island topology to minimize the number of capacitors required to supply the burst current needs of the termination rail.
- See the Micron DesignLine publication entitled *Decoupling Capacitor Calculation for a DDR Memory Channel* (`http://download.micron.com/pdf/pubs/designline/3Q00dl1-4.pdf`).

3.5.3 General Routing

The general routing considerations for the DDR are as follows:

- All DDR signals must be routed next to a solid reference:
  - For data, next to solid ground planes.
  - For address/command, power planes if necessary.
- All DDR signals must be impedance controlled. This is system dependent, but typical values are 50–60 ohm.
- Minimize other cross-talk opportunities. As possible, maintain at least a four times the trace width spacing between all DDR signals to non-DDR signals.
- Keep the number of vias to a minimum to eliminate additional stubs and capacitance.
- Signal group routing priorities are as follows:
  - DDR clocks.
  - Route MVTT/MVREF.
  - Data group.
  - Command/address.
- Minimize data bit jitter by trace matching.

3.5.4 Routing Clock Distribution

The DDR clock distribution considerations are as follows:

- DDR controller supports six clock pairs:
  - 2 DIMM modules.
  - Up to 36 discrete chips.
- For route traces as for any other differential signals:
  - Maintain proper difference pair spacing.
  - Match pair traces within 25 mm.
- Match all clock traces to within 100 mm.
- Keep all clocks equally loaded in the system.
- Route clocks on inner critical layers.

3.5.5 Data Routing

The DDR data routing considerations are as follows:

- Route each data group (8-bits data + DQS + DM) on the same layer. Avoid switching layers within a byte group.
- Take care to match trace lengths, which is extremely important.
- To make trace matching easier, let adjacent groups be routed on alternate critical layers.
- Pin swap bits within a byte group to facilitate routing (discrete case).
- Tight trace matching is recommended within the DDR data group. Keep each 8-bit datum and its DM signal within ± 25 mm of its respective strobe.
- Minimize lengths across the entire DDR channel:
  - Between all groups maintain a delta of no more than 500 mm.
  - Allows greater flexibility in the design for readjustments as needed.
- DDR data group separation:
  - If stack-up allows, keep DDR data groups away from the address and control nets.
  - Route address and control on separate critical layers.
  - If resistor networks (RNs) are used, attempt to keep data and command lines in separate packages.